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APPLICATION NO.	F	ILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/013,087		12/07/2001	Hideyuki Andoh	44471-267680 (13700)	1427
23370	7590	03/07/2006		EXAMINER	
JOHN S. P			SCHILLINGER, LAURA M		
KILPATRICK STOCKTON, LLP 1100 PEACHTREE STREET				ART UNIT	PAPER NUMBER
ATLANTA,	GA 303	309	2813	**	
				DATE MAILED: 03/07/2000	6

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)			
ü t	10/013,087	ANDOH, HIDEYUKI			
Office Action Summary	Examiner	Art Unit			
	Laura M. Schillinger	2813			
The MAILING DATE of this communication Period for Reply	appears on the cover sheet wit	th the correspondence address			
A SHORTENED STATUTORY PERIOD FOR RE WHICHEVER IS LONGER, FROM THE MAILING - Extensions of time may be available under the provisions of 37 CFR after SIX (6) MONTHS from the mailing date of this communication. - If NO period for reply is specified above, the maximum statutory per - Failure to reply within the set or extended period for reply will, by state Any reply received by the Office later than three months after the meanned patent term adjustment. See 37 CFR 1.704(b).	B DATE OF THIS COMMUNIC R 1.136(a). In no event, however, may a re- riod will apply and will expire SIX (6) MONT atute, cause the application to become ABA	CATION. Poply be timely filed THS from the mailing date of this communication. ANDONED (35 U.S.C. § 133).			
Status					
1) Responsive to communication(s) filed on 1-	4 December 2005.				
2a) ☐ This action is FINAL . 2b) ☑ T	This action is FINAL. 2b)⊠ This action is non-final.				
3) Since this application is in condition for allowance except for formal matters, prosecution as to					
closed in accordance with the practice unde	er <i>Ex parte Quayle</i> , 1935 C.D.	. 11, 453 O.G. 213.			
Disposition of Claims					
4) ⊠ Claim(s) 1-9 is/are pending in the application 4a) Of the above claim(s) is/are without 5) □ Claim(s) is/are allowed. 6) ⊠ Claim(s) 1-9 is/are rejected. 7) □ Claim(s) is/are objected to. 8) □ Claim(s) are subject to restriction and	drawn from consideration.				
Application Papers					
9)☐ The specification is objected to by the Exam	niner.				
10) The drawing(s) filed on is/are: a) a	accepted or b) Objected to b	by the Examiner.			
Applicant may not request that any objection to	= • •				
Replacement drawing sheet(s) including the cor					
11) ☐ The oath or declaration is objected to by the	Examiner. Note the attached	Office Action of form P10-152.			
Priority under 35 U.S.C. § 119					
 12) Acknowledgment is made of a claim for fore a) All b) Some * c) None of: 1. Certified copies of the priority docum 2. Certified copies of the priority docum 3. Copies of the certified copies of the priority 	ents have been received. ents have been received in Ap	pplication No			
application from the International Bur	reau (PCT Rule 17.2(a)).				
* See the attached detailed Office action for a	list of the certified copies not I	received.			
Attachmont/c)					
Attachment(s) 1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948)		ummary (PTO-413))/Mail Date			

U.S. Patent and Trademark Office PTOL-326 (Rev. 7-05)

Paper No(s)/Mail Date 12/24/05.

3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)

6) Other: _

5) Notice of Informal Patent Application (PTO-152)

DETAILED ACTION

Allowability is hereby withdrawn, in view of newly discovered prior art.

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claims 1-9 are rejected under 35 U.S.C. 102(b) as being anticipated by Yanagisawa (JP 58-085572).

In reference to claim 1, Yanagisawa teaches a device comprising:

A first semiconductor region of a first conductivity type, defined by an upper end surface and a side boundary surface connecting the upper and lower end surfaces when viewed in section (Fig.D (16));

A second semiconductor region of the first conductivity type disposed under the first semiconductor region and being in contact with the lower end surface of the first semiconductor region so as to share a common boundary surface by the first and second semiconductor regions (Fig.D (12));

A third semiconductor region of a second conductivity type disposed on the first semiconductor region and being in contact with the upper end surface of the first semiconductor region (Fig.D (18)); and

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A fourth semiconductor region having inner surface in contact with the first and second with the side boundary surface when viewed in section and an impurity concentration lower than the first semiconductor region, configured such that the fourth semiconductor region is disposed between the second and third semiconductor regions (Fig.D (13)) (see abstract).

In reference to claim 2, Yanagisawa teaches wherein the fourth semiconductor region has a first type conductivity (Fig.D (13)).

In reference to claim 3, Yanagisawa teaches wherein outer surface of the fourth semiconductor region serves as a chip outer surface of the semiconductor device and the chip outer surface is substantially orthogonal with the lower end surface of the first semiconductor region (Fig.D (13)).

In reference to claim 4, Yanagisawa teaches wherein the fourth semiconductor region is made of a wafer cut from bulk crystal (inherent- semiconductor substrates are made from wafers cut from bulk crystal).

In reference to claim 5, Yanagisawa teaches further comprising a first main electrode layer is formed on a bottom surface of the second semiconductor region (Fig.G (21)).

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In reference to claim 6, Yanagisawa teaches wherein the first main electrode layer is contacted with the second semiconductor region, through a first concavity formed at the bottom surface of the second semiconductor region (Fig.G (21)).

In reference to claim 7, Yanagisawa teaches further comprising a first main electrode layer, a part of the first main electrode layer is buried in a via hole penetrating through the second semiconductor region, configured such that the buried part of the first main electrode layer contacts with the first semiconductor region (Fig.G (21)).

In reference to claim 8, Yanagisawa teaches further comprising a second main electrode layer is formed on a top surface of the third semiconductor region (Fig.G (20)).

In reference to claim 9, Yanagisawa teaches wherein the second main electrode layer is contacted with the first semiconductor regions, through a second concavity formed at the top surface of the third semiconductor region (Fig.G (20)).

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Laura M. Schillinger whose telephone number is (571) 272-1697. The examiner can normally be reached on M-T, R-F 7:00-5:00.

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If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Carl W. Whitehead, Jr. can be reached on (571) 272-1702. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

02/27/06

Laura M Schillinger
Primary Examiner
Art Unit 2813